

SNP Microchip Series High Performances IR Lasers



KEY FEATURES

- Repetition rate up to 130 kHz
- Ultrashort pulses down to 600 ps
- Multi-kW peak power
- Excellent beam quality – TEM₀₀, $M^2 < 1.3$
- Efficient, air-cooled
- Sealed package, extremely long life

For generating high peak power IR pulses of a few hundred picoseconds, microchip lasers are economical, compact, and reliable. Sub-nanosecond 1064 nm pulses are indeed directly generated from the diode pumped passively Q-switched Nd:YAG microchip engine. Microchips are also easy to operate and service ; controllers can be used with every laser head model and swapped within minutes while conserving constant performances. The SNP series are designed for high average power, either from pulse energies of 20 μ J at 1064 nm, or from repetition rates up to 130 kHz.

APPLICATIONS

- LIDAR & Range Finding
- 3D Time-of-Flight Imaging
- LIBS / Micro-LIBS
- Precision Micromachining
- Laser Micromarking
- Photoacoustic Applications
- Nonlinear Optics & OPO Pumping
- Optical Damage Testing
- Pulsed Optical Instrumentation
- Amplifier Seeding

TECHNICAL SPECIFICATIONS

	SNP-08E-100	SNP-18E-100	SNP-20F-100	SNP-50F-100	SNP-130F-100	SNP-200P-100	SNP-300P-100
Wavelength	1064nm	1064nm	1064nm	1064nm	1064nm	1064nm	1064nm
Repetition Rate	>5kHz	>13kHz	>19kHz	>45kHz	>130kHz	>19 KHz	>29 KHz
Constant Pulse width range (FWHM)⁽¹⁾	<1ns	>3ns	<1ns	<0.7ns	<1.4ns	<0.85 ns	<0.75 ns
Output power⁽²⁾	>40mW	>300mW	>140mW	>190mW	>200mW	>200mW	>300mW
Output energy	>8μJ	>18μJ	>7μJ	>4μJ	>1.5μJ	>11μJ	>9.5μJ
Peak Power	>8kW	N/A	>10kW	>5.5kW	>1.1kW	>13kW	>13kW
Short term (10min) power stability⁽³⁾	<±1%	<±2%	<±1%	<±1%	<±1%	<±1%	<±1%
Long term (6 hrs) power stability⁽³⁾	<±3%	<±5%	<±3%	<±3%	<±3%	<±3%	<±3%
Beam profile	Gaussian TEM00	Gaussian TEM00	Gaussian TEM00	Gaussian TEM00	Gaussian TEM00	Gaussian TEM00	Gaussian TEM00
Full angle divergence							
Horizt.@1/e²	12 ± 2 mrad	5.2±1 mrad	13±5mrad	17±3mrad	17±2.5mrad	13±2mrad	15±2mrad
Vertical@1/e²	14 ± 2 mrad	5.1±1 mrad	13±5mrad	17±3mrad	17±2.5mrad	13±2mrad	15±3mrad
M²⁽⁴⁾	<1.3	<1.3	<1.3	<1.3	<1.3	<1.3	<1.3
Beam ellipticity⁽⁵⁾	<1.3	<1.3	<1.3	<1.3	<1.3	<1.2	<1.2
Polarization	Linear PER>20dB	Elliptical ⁽⁶⁾	Linear PER>20dB	Linear PER>20dB	Linear PER>20dB	Linear PER>20dB	Linear PER>20dB
Package dimensions	115x29x36 mm	145x42x36 mm	145x42x36 mm	145x42x36 mm	145x42x36 mm	145x42x36 mm	145x42x36 mm
Package weight	250g	300g	300g	300g	300g	300g	300g
Options (table p3)	None	C	F,M,S	F,M,S	F,M,S	F,M,S	F,M,S

NOTES

(1) Measured with 1Ghz photodiode and 1GHz/10GS/s oscilloscope.

(2) Measurement performed with an OPHIR thermal power sensor (OPHIR 3A-FS-SH)

(3) For temperature variation < ± 3°C and < 3°C/hour, stability is measured with calorimeter - detector band [DC, 2Hz]

(4) Mean average value $M = \sqrt{\langle XY \rangle}$, X and Y being respectively the major and minor axis of the ellipse

(5) Beam ellipticity is calculated as the ratio of the main axis far field divergence

(6) Linear polarization available as an option

COMPLEMENTARY INFORMATION & OPTIONS

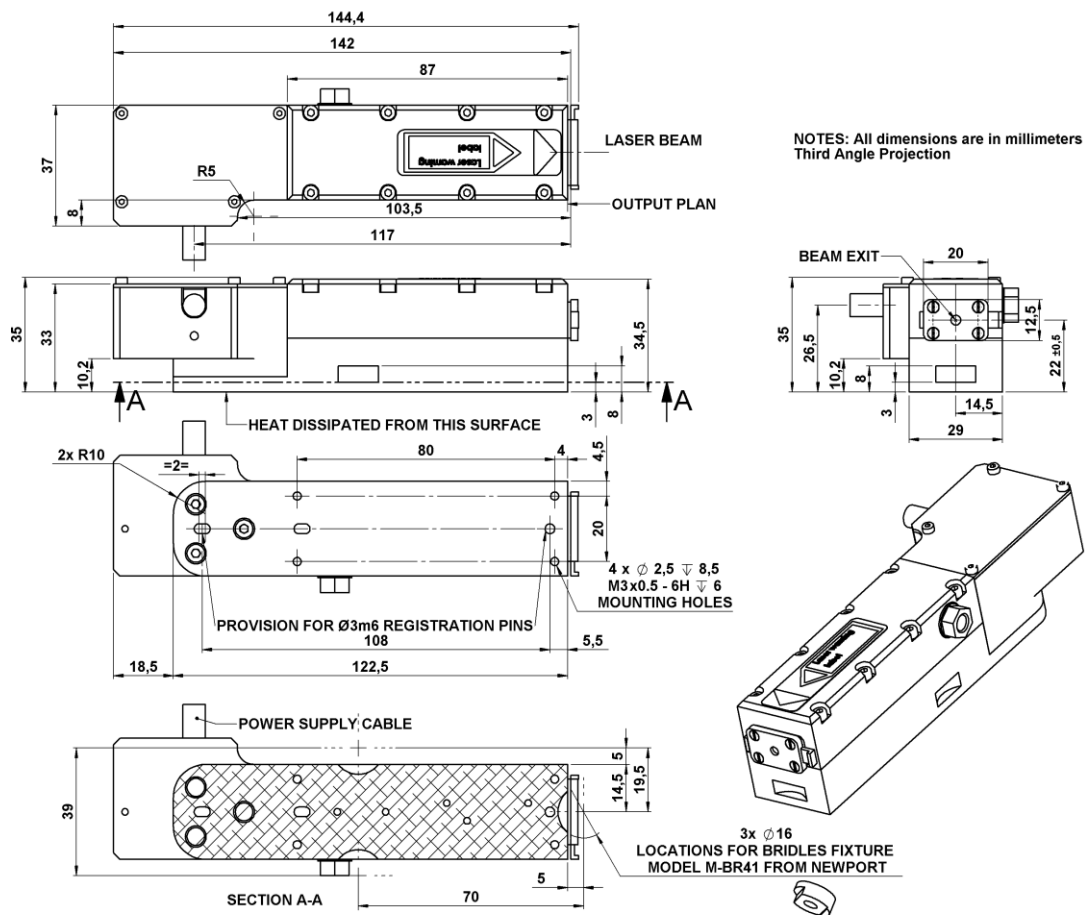
Environment Parameters	
Operating Temperature Range	0-50°C
Maximum Laser Head Baseplate Temperature	<50°C
Maximum Power Consumption	<40W
Laser Head Thermal Dissipation	<15W
Storage Temperature	0-50°C
Shock of 11ms according to IEC 68-2-27, non operating	25g
Vibration 5Hz to 500Hz sinusoidal according to IEC 68-2-6	2g

Certification	
Laser classification according to IEC 60825-1:2014	3B
CDRH	Yes, if used with a -DR1 controller
RoHS	Yes

Options	
Multimode fibering (M)	Contact factory for details
Single mode fibering (F)	Contact factory for details
Synchronization output (S)	Contact factory for details
Collimation (C)	Contact factory for details

Available Controller Types			
Model	Type	Input Power	CDRH
MLC-03A-DR1	Desktop	100-240 V AC	Yes
MLC-03A-MR1	Module	12 V DC	No
MLC-03A-BR1	Board	12 V DC	No

CDRH LASER HEAD MECHANICAL DRAWINGS: SNP-18E-100, SNP-20F-100, SNP-50F-100, SNP-130F-100, SNP-200P-100, SNP-300P-100



CDRH LASER HEAD MECHANICAL DRAWINGS: SNP-08E-100

